

isc N-Channel MOSFET Transistor

IXTK33N50

FEATURES

- · Drain Source Voltage-
 - : V_{DSS}= 500V(Min)
- Static drain-source on-resistance
 - : RDS(on) \leq 60m Ω @V_{GS}=10V
- · 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation



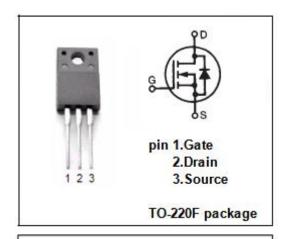
- DC/DC Converter
- · Ideal for high-frequency switching and synchronous rectification

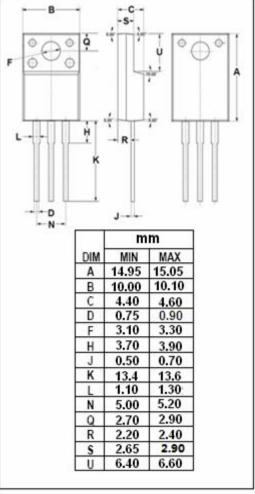
• ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

SYMBOL	PARAMETER	VALUE	UNIT	
V _{DSS}	Drain-Source Voltage	ain-Source Voltage 500		
V _{GS}	Gate-Source Voltage	±20	٧	
l _D	Drain Current-Continuous 33		Α	
I _{DM}	Drain Current-Single Pulsed	Current-Single Pulsed 132		
P _D	Total Dissipation @T _C =25℃	416	W	
Tj	Operating Junction Temperature	-55~150	$^{\circ}\!\mathbb{C}$	
T _{stg}	Storage Temperature	-55~150	$^{\circ}$	

• THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th(j-c)}$	Junction-to-case thermal resistance	0.3	°C/W







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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V; ID =5mA	500		V
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} ; ID =250 μ A	2	4	V
R _{DS(on)}	Drain-Source On-Resistance	V _{GS} =10V; I _D = 25A		60	mΩ
I _{GSS}	Gate-Source Leakage Current	V _{GS} = ±20V;V _{DS} =0V		±100	nA
I _{DSS}	Drain-Source Leakage Current	V _{DS} = 400V; V _{GS} = 0V		200	- μ Α
		V _{DS} = 400V; V _{GS} = 0V;T _J =125°C		3000	
V _{SD}	Diode forward voltage	I _F = 33A; V _{GS} = 0V		1.5	V



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